### 1. General description

PNP high-voltage low  $V_{CEsat}$  transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8215Z

#### 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- Medium power SMD plastic package
- AEC-Q101 qualified

### 3. Applications

- LED driver for LED chain module
- LCD backlighting
- · Automotive motor management
- Switch Mode Power Supply (SMPS)

#### 4. Quick reference data

#### Table 1. Quick reference data

| Symbol           | Parameter                 | Conditions  |  | Min | Тур | Max  | Unit |
|------------------|---------------------------|---|--|-----|-----|------|------|
| V <sub>CEO</sub> | collector-emitter voltage | open base   |  | -   | -   | -150 | V    |
| Ic               | collector current         |   |  | -   | -   | -2   | Α    |
| h <sub>FE</sub>  | DC current gain           | $V_{CE}$ = -10 V; $I_{C}$ = -100 mA; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ = 0.02; $T_{amb}$ = 25 °C |  | 100 | 180 | -    |      |

# 5. Pinning information

**Table 2. Pinning information** 

| Pin | Symbol | Description | Simplified outline               | Graphic symbol |
|-----|--------|-------------|----------------------------------|----------------|
| 1   | В      | base        | 4                                | C              |
| 2   | С      | collector   |                                  | В              |
| 3   | Е      | emitter     |                                  | □ — h          |
| 4   | С      | collector   | <b>∃</b> 1 <b>∃</b> 2 <b>∃</b> 3 | Ė              |
|     |        |             | SC-73 (SOT223)                   | sym028         |



### 150 V, 2 A PNP high-voltage low VCEsat transistor

# 6. Ordering information

#### **Table 3. Ordering information**

| Type number | Package |   |               |
|-------------|---------|---|---------------|
|             | Name    | Description   | Version       |
| PBHV9215Z   |         | plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body | <u>SOT223</u> |

### 7. Marking

#### Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBHV9215Z   | V9215Z       |

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

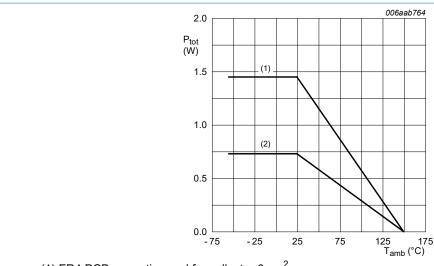
| Symbol           | Parameter                 | Conditions                          |     | Min | Max  | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                        |     | -   | -200 | V    |
| $V_{CEO}$        | collector-emitter voltage | open base                           |     | -   | -150 | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                      |     | -   | -6   | V    |
| I <sub>C</sub>   | collector current         |                                     |     | -   | -2   | А    |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | -4   | А    |
| I <sub>BM</sub>  | peak base current         |                                     |     | -   | -500 | mA   |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 0.73 | W    |
|                  |                           |                                     | [2] | -   | 1.45 | W    |
| Tj               | junction temperature      |                                     |     | -   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |     | -65 | 150  | °C   |

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

PBHV9215Z

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

#### 150 V, 2 A PNP high-voltage low VCEsat transistor



- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, standard footprint

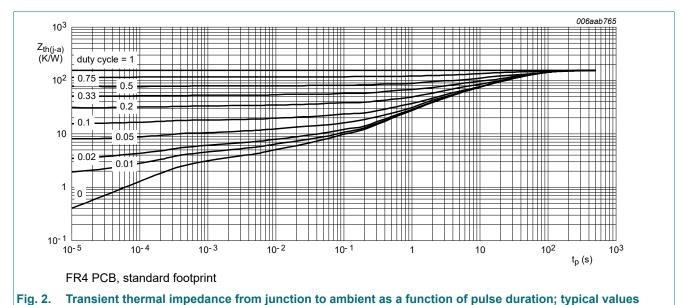
Fig. 1. Power derating curves

### 9. Thermal characteristics

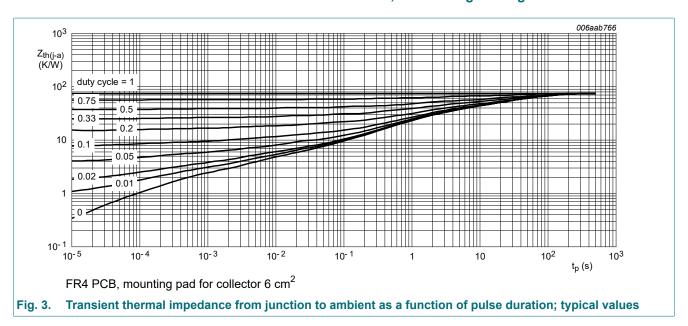
**Table 6. Thermal characteristics** 

| Symbol                | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub>  | thermal resistance from                          | in free air | [1] | -   | -   | 170 | K/W  |
|                       | junction to ambient                              |             | [2] | -   | -   | 85  | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |             |     | -   | -   | 15  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



#### 150 V, 2 A PNP high-voltage low VCEsat transistor



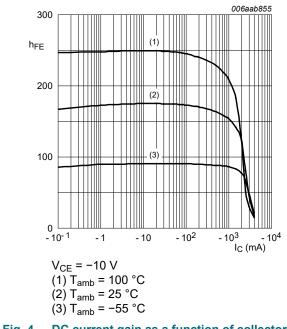
### 10. Characteristics

**Table 7. Characteristics** 

| Symbol             | Parameter                               | Conditions  | Min | Тур  | Max   | Unit |
|--------------------|---|---|-----|------|-------|------|
| I <sub>CBO</sub>   | collector-base cut-off                  | V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C                            | -   | -    | -100  | nA   |
|                    | current                                 | V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C                             | -   | -    | -10   | μΑ   |
| I <sub>EBO</sub>   | emitter-base cut-off current            | $V_{EB} = -4 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$                                 | -   | -    | -100  | nA   |
| I <sub>CES</sub>   | collector-emitter cut-off current       | V <sub>CE</sub> = -120 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C                           | -   | -    | -100  | nA   |
| h <sub>FE</sub>    | DC current gain                         | $V_{CE}$ = -10 V; $I_{C}$ = -100 mA; pulsed; $t_{p} \le$ 300 μs; $\delta$ = 0.02; $T_{amb}$ = 25 °C | 100 | 180  | -     |      |
|                    |   | $V_{CE}$ = -10 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ = 0.02; $T_{amb}$ = 25 °C      | 80  | 155  | -     |      |
|                    |   | $V_{CE}$ = -10 V; $I_{C}$ = -1.5 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ = 0.02; $T_{amb}$ = 25 °C    | 70  | 140  | -     |      |
|                    |   | $V_{CE}$ = -10 V; $I_{C}$ = -2 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ = 0.02; $T_{amb}$ = 25 °C      | 60  | 120  | -     |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage    | $I_C$ = -100 mA; $I_B$ = -20 mA; pulsed; $t_p \le$ 300 μs; δ = 0.02; $T_{amb}$ = 25 °C              | -   | -25  | -50   | mV   |
|                    |   | $I_C$ = -1 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ = 0.02; $T_{amb}$ = 25 °C                  | -   | -110 | -190  | mV   |
|                    |   | $I_C$ = -1.5 A; $I_B$ = -300 mA; pulsed; $t_p \le$ 300 μs; δ = 0.02; $T_{amb}$ = 25 °C              | -   | -155 | -270  | mV   |
|                    |   | $I_C$ = -2 A; $I_B$ = -400 mA; pulsed; $t_p$ ≤ 300 μs; δ = 0.02; $T_{amb}$ = 25 °C                  | -   | -200 | -350  | mV   |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $I_C$ = -2 A; $I_B$ = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                | -   | 100  | 175   | mΩ   |
| $V_{BEsat}$        | base-emitter saturation voltage         |   | -   | -1   | -1.15 | V    |

### 150 V, 2 A PNP high-voltage low VCEsat transistor

| Symbol           | Parameter             | Conditions   | Min | Тур  | Max | Unit |
|------------------|-----------------------|--|-----|------|-----|------|
| t <sub>d</sub>   | delay time            | V <sub>CC</sub> = -6 V; I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = -0.1 A;                                  | -   | 20   | -   | ns   |
| t <sub>r</sub>   | rise time             | I <sub>Boff</sub> = 0.1 A; T <sub>amb</sub> = 25 °C  | -   | 105  | -   | ns   |
| t <sub>on</sub>  | turn-on time          |  | -   | 125  | -   | ns   |
| t <sub>s</sub>   | storage time          |  | -   | 875  | -   | ns   |
| t <sub>f</sub>   | fall time             |  | -   | 150  | -   | ns   |
| t <sub>off</sub> | turn-off time         |  | -   | 1025 | -   | ns   |
| f <sub>T</sub>   | transition frequency  | $V_{CE}$ = -10 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C   | -   | 35   | -   | MHz  |
| C <sub>c</sub>   | collector capacitance | V <sub>CB</sub> = -20 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C  | -   | 30   | -   | pF   |
| C <sub>e</sub>   | emitter capacitance   | V <sub>EB</sub> = -0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C | -   | 530  | -   | pF   |

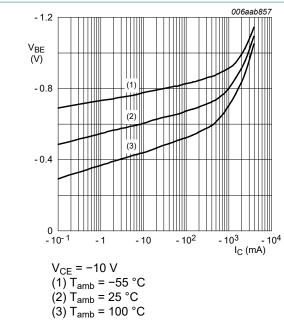


-4.0 I<sub>B</sub> (mA) = -360 I<sub>C</sub> (A) 252 - 288 - 3.2 - 216 - 180 - 108 36 - 1.6 - 0.8 0 - 1 -4<sub>VCE</sub> (V) -5 - 2 - 3  $T_{amb}$  = 25 °C

006aab856

Fig. 5. Collector current as a function of collectoremitter voltage; typical values

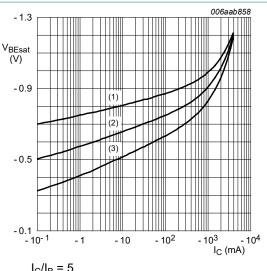
#### 150 V, 2 A PNP high-voltage low VCEsat transistor



(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



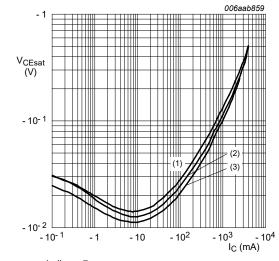
$$I_{\rm C}/I_{\rm B} = 5$$

(1) 
$$T_{amb} = -55 \,^{\circ}\text{C}$$
  
(2)  $T_{amb} = 25 \,^{\circ}\text{C}$   
(3)  $T_{amb} = 100 \,^{\circ}\text{C}$ 

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



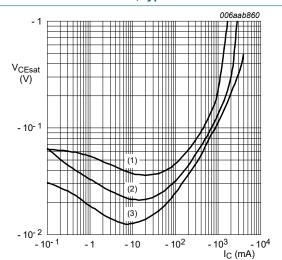
$$I_{\rm C}/I_{\rm B}=5$$

$$(1) T_{amb} = 100 °C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 20$$

(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

#### 150 V, 2 A PNP high-voltage low VCEsat transistor

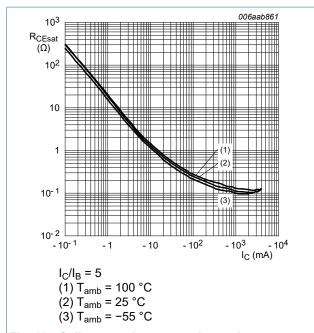


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

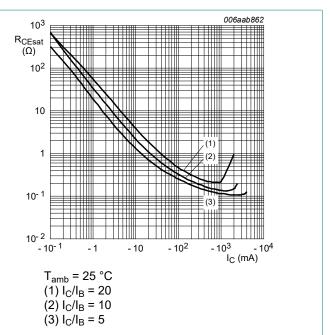
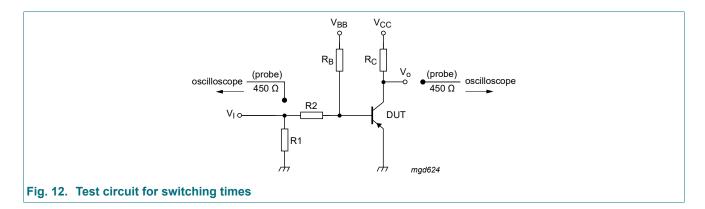


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

### 11. Test information

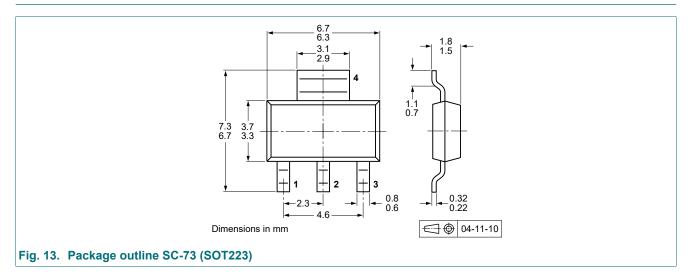


#### **Quality information**

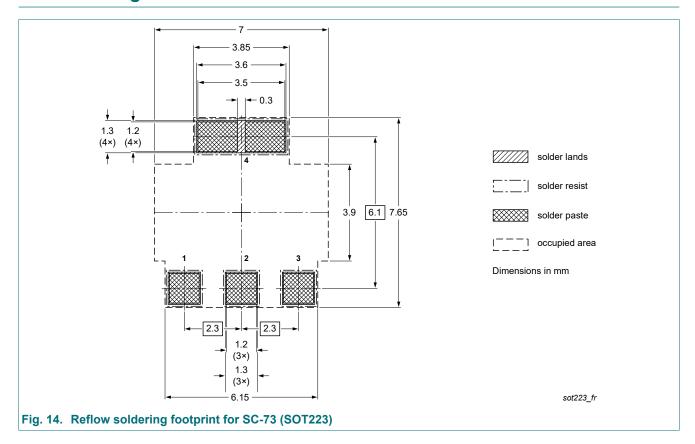
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

150 V, 2 A PNP high-voltage low VCEsat transistor

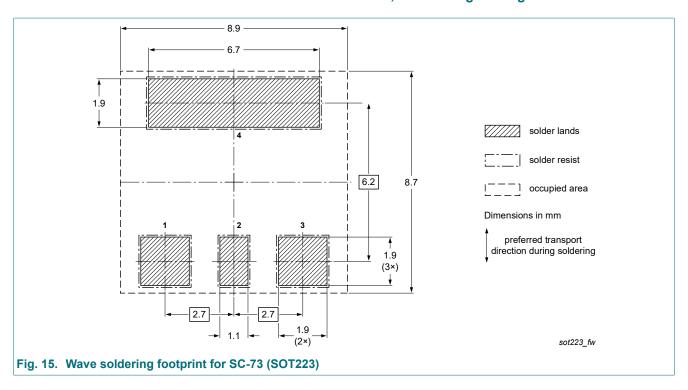
# 12. Package outline



# 13. Soldering



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### 150 V, 2 A PNP high-voltage low VCEsat transistor

# 14. Revision history

#### **Table 8. Revision history**

| Data sheet ID  | Release date               | Data sheet status   | Change notice | Supersedes  |  |  |
|----------------|----------------------------|---|---------------|-------------|--|--|
| PBHV9215Z v.2  | 20230717                   | Product data sheet  | -             | PBHV9215Z_1 |  |  |
| Modifications: | Nexperia. • Legal texts ha | <ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Section "Packing information" removed.</li> </ul> |               |             |  |  |
| PBHV9215Z_1    | 20091211                   | Product data sheet  | -             | -           |  |  |

### 15. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 17 July 2023

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